Infrared Laser Diode

Part No: LD-850-80-50-A-2

Features

※ Wavelength: λ=850nm(Type)
※ Low threshold current: Ith=40mA(Type)
※ Output optical power: 80mW(CW)
※ Package: TO-18(Φ5.6mm)

Applications

※ Industrial Use

Absolute Maximum Rating at Tc=25℃

Items	Symbols	Values	Unit
Optical Output Power	Po(CW)	80	mW
	Vr(LD)	2	V
Operating Temperature	Topr	-10~+50	℃
Storage Temperature	Tstg	-40~+80	℃

Electrical and Optical Characteristics at Tc=25℃

Items	Symbols	Min	Type	Max.	Unit	Condition
Threshold Current	Ith	-	25	35	mA	CW
Operating Current	Iop	-	155	180	mA	Po=80mW
Operating Voltage	Vop	-	2	2.1	V	Po=80mW
Slope Efficiency	SE	0.5	0.9	-	mW/mA	Po=80mW
Lasing Wavelength	λ	840	850	860	nm	Po=80mW
Beam Divergence	//	10	12	14	°	Po=80mW
	⊥	33	35	40	°	Po=80mW
Beam Angle	△//	-	-	±3	°	Po=80mW
	△⊥	-	-	±3	°	Po=80mW
Emission Point Accuracy	△X△Y△Z	-80	-	80	um	Po=80mW

1)Measurement condition: CW
2)Full angle at half maximum.
3)All the above values are measured by OPELUS metheod.

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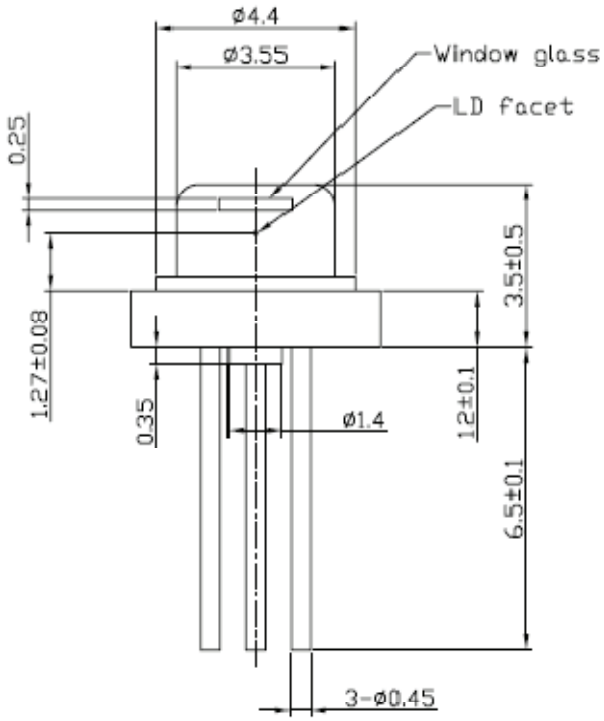
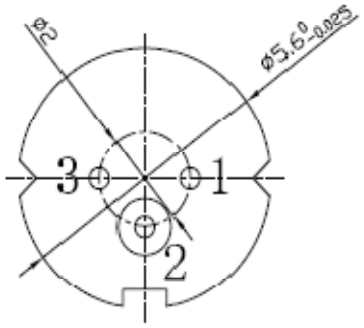
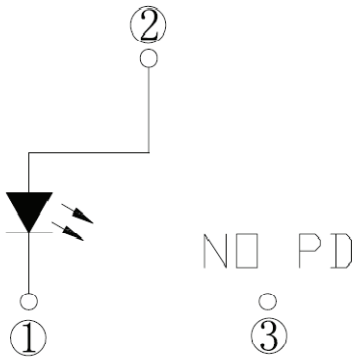
Package and Electrical connection







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